

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 09-181195

(43)Date of publication of application : 11.07.1997

(51)Int.Cl. H01L 21/8238
H01L 27/092
H01L 27/04
H01L 21/822

(21)Application number : 08-320042

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(22)Date of filing : 29.11.1996

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(30)Priority

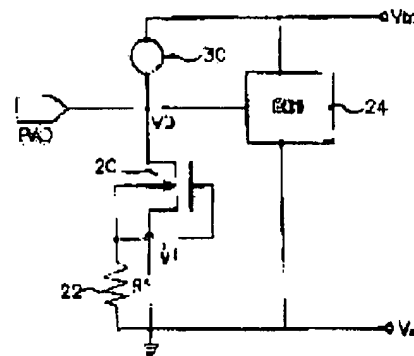
Priority number : 95 9546232 Priority date : 02.12.1995 Priority country : KR

(54) ELECTROSTATIC PROTECTIVE DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain an electrostatic protective device which prevents a current concentration phenomenon and whose electrostatic protective performance is enhanced by a method wherein the gate of a MOS element is grounded through an internal resistor.

SOLUTION: An electrostatic protective device 30 is connected across the input end and the output end of an internal circuit 24 which is situated between a first power-supply voltage source VDD and a second power-supply voltage source VSS. The electrostatic protective device 30 is provided with a drain which is formed on a well region, which is connected to the input end and the output end of the internal circuit 24 and to which the first power-supply voltage source VDD is applied, with a source which is connected in common across the second power-supply voltage source VSS and the well region and with a MOS element 20 which is connected to a well contact part and which has a gate. In addition, the electrostatic protective device is provided with an internal resistor 22 connected to the gate of the MOS element 20 through the well contact part. For example, a MOS element 20 is an N-channel conductivity-type MOS transistor. In addition, an internal resistance 22 is formed as a well resistance, and its resistance value is set at several Ω to several hundred Ω .



LEGAL STATUS

[Date of request for examination] 28.09.2001

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than

Searching PAJ

페이지 2 / 2

the examiner's decision of rejection or
application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision
of rejection]

[Date of requesting appeal against examiner's
decision of rejection]

[Date of extinction of right]

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